



Product data sheet

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SOT-23-3L

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Features

- -20V,-3A, RDS(ON) =60mΩ@VGS = -4.5V
- Improved dv/dt capability
- Fast switching
- Green Device Available

Applications

- Notebook
- Load Switch
- Battery Protection
- Hand-held Instruments

BVDSS	RDSON	ID
-20V	$60 \text{m}\Omega$	-3A

Absolute Maximum Ratings Tc=25 unless otherwise noted

Symbol	Parameter	Rating	Units
Vds	Drain-Source Voltage	-20	V
Vgs	Gate-Source Voltage	±12	V
	Drain Current – Continuous (T _c =250)	-3.0	A
D	Drain Current – Continuous (T _c =1000)	-2.0	A
l _{DM}	Drain Current – Pulsed ¹	-12	A
	Power Dissipation (T _c =250)	1.56	W
P _D	Power Dissipation – Derate above 250	0.012	W/ C
T _{STG}	Storage Temperature Range	-55 to 150	С
TJ	Operating Junction Temperature Range	-55 to 150	С

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
R _{0JA}	Thermal Resistance Junction to ambient		80	C/W



Off Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-20			V
	BV _{DSS} Temperature Coefficient	Reference to 250 , I _D =-1mA		-0.01		V/ C
	Dursin Service Legicene Crument	V _{DS} =-20V , V _{GS} =0V , T _J =250			-1	uA
IDSS	Drain-Source Leakage Current	V _{DS} =-16V , V _{GS} =0V , T _J =1250			-10	uA
lgss	Gate-Source Leakage Current	V_{GS} = ±12V , V_{DS} =0V			±10	uA

On Characteristics

R _{DS(ON)}	RDS(ON) Static Drain-Source On-Resistance	V _{GS} =-4.5V , I _D =-3A		60	80	mΩ
	V _{GS} =-2.5V , I _D =-2A		80	120	1122	
V _{GS(th)}	Gate Threshold Voltage		-0.3	-0.65	-1.1	V
${}^{\vartriangle}V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	─V _{GS} =V _{DS} , I _D =-250uA		3		mV/ C
gfs	Forward Transconductance	V _{DS} =-10V , I _S =-1A		2.2		S

Dynamic and switching Characteristics

Qg	Total Gate Charge ^{2,3}		 4.8	
Q _{gs}	Gate-Source Charge ^{2,3}	$V_{\text{DS}}\text{=-10V}$, $V_{\text{GS}}\text{=-4.5V}$, $I_{\text{D}}\text{=-3A}$	 0.5	 nC
Q_{gd}	Gate-Drain Charge ^{2,3}		 1.9	
T _{d(on)}	Turn-On Delay Time ^{2 , 3}		 3.5	
Tr	Rise Time ^{2,3}	V_{DD} =-10V , V_{GS} =-4.5V , R_G =25 Ω	 12.6	
T _{d(off)}	Turn-Off Delay Time ^{2,3}	I _D =-1A	 32.6	 nS
T _f	Fall Time ^{2,3}		 8.4	
C _{iss}	Input Capacitance		 550	
Coss	Output Capacitance	$V_{\text{DS}}\text{=-10V}$, $V_{\text{GS}}\text{=}0\text{V}$, F=1MHz	 65	 pF
Crss	Reverse Transfer Capacitance		 55	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
ls	Continuous Source Current				-3.0	А
Іѕм	Pulsed Source Current	V _G =V _D =0V , Force Current			-13	А
Vsd	Diode Forward Voltage	V_{GS} =0V , I_{S} =-1A , T_{J} =25C			-1.2	V

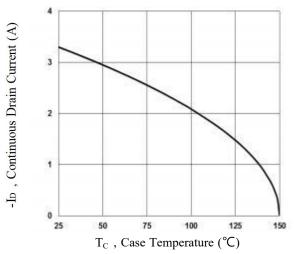
Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.

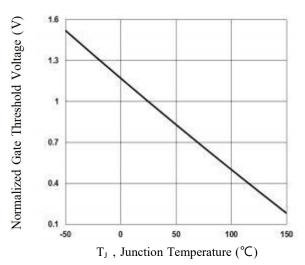
2. The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%.

3. Essentially independent of operating temperature.

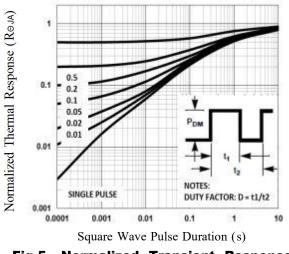














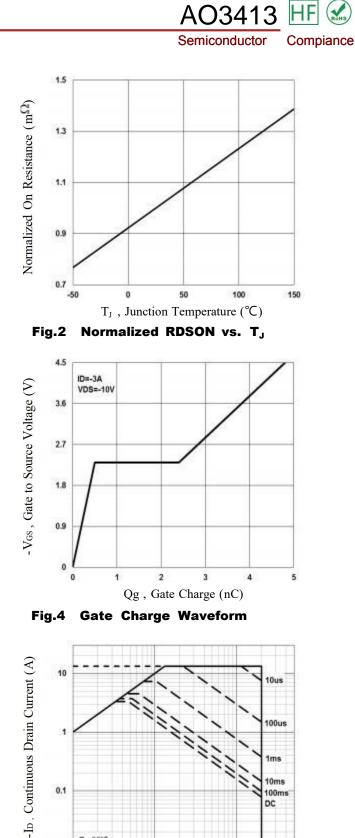


Fig.6 Maximum Safe Operation Area

-V_{DS}, Drain to Source Voltage (V)

1

0.1

0.01

0.1

Tc=25°C

10ms

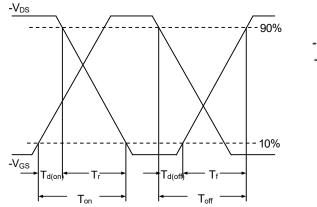
100ms DC

10



Fig.7

AO3413 HF RoHS Semiconductor Compiance



Switching Time Waveform

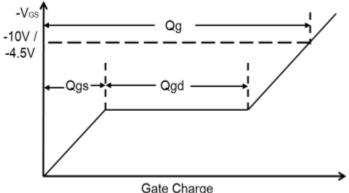
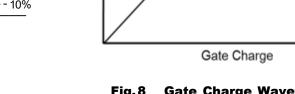


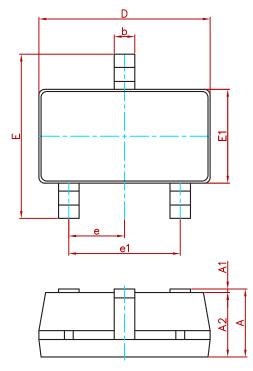
Fig.8 **Gate Charge Waveform**

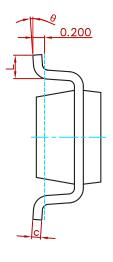






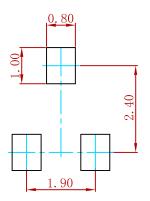
PACKAGE MECHANICAL DATA





Symbol	ymbol Dimensions In Millimeters Min. Max.		Dimension	s In Inches
Symbol			Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
е	0.950(BSC)	0.037((BSC)
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:

1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
AO3413	SOT-23-3L	3000





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